AMENDMENTS TO THE CLAIMS

This listing of claims replaces all prior listing of claims in this application.

Claims 1-25 (canceled).

26. (currently amended) A composition suitable for use in etching an insulative layer formed over a substrate in a semiconductor device, said composition ~~comprising~~ consisting essentially of:

a flowing plasma etchant mixture consisting essentially of at least one fluorocarbon and ammonia, wherein the flow rate ratio of each fluorocarbon to ammonia is from about ~~2:1~~ 3:1 to about 40:1.

27. (previously presented) The composition of claim 26, wherein said fluorocarbon is at least one member selected from the group consisting of fluorohydrocarbons, chlorofluorocarbons and chlorofluorohydrocarbons.

28. (original) The composition of claim 27, wherein said fluorocarbon is at least one member selected from the group consisting of C_4F_8, C_4F_6, C_5F_8, CF_4, C_2F_6, C_3F_8, CHF_3, and CH_2F_2.

29. (original) The composition of claim 26, wherein said fluorocarbon is at least one member selected from the group consisting of CF_4, CHF_3, and CH_2F_2.

30. (original) The composition of claim 29, wherein said fluorocarbon is at least two members selected from the group consisting of CF_4, CHF_3, and CH_2F_2.

31. (original) The composition of claim 30, wherein said fluorocarbon is a combination of CF_4, CHF_3, and CH_2F_2.

32. (previously presented) The composition of claim 26, wherein said composition is ineffective to remove side wall spacers of a gate stack formed over said substrate.

33. (canceled).

34. (previously presented) The composition of claim 26, wherein said flow rate ratio is within the range of from about 3:1 to about 20:1.

35. (previously presented) The composition of claim 34, wherein said flow rate ratio is within the range of from about 4:1 to about 10:1.

Claims 36-70 (canceled).

71. (previously presented) A composition suitable for use in etching an insulative layer formed on a substrate in a semiconductor device, said composition comprising:

a flowing plasma etchant mixture comprising at least CF_4 and NH_3, wherein the flow rate ratio of said CF_4:NH_3 is greater than about 3:1.

72. (previously presented) A composition suitable for use in etching an insulative layer formed on a substrate in a semiconductor device, said composition comprising:

a flowing plasma etchant mixture comprising at least CHF_3 and ammonia, wherein the flow rate of said CHF_3 is from about 37 to 42 sccm.

Claims 73-76 (canceled).